



**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.7	C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	50	C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	C

**Electrical Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 80V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 10A$				
		$V_{GS} = 4.5V, I_D = 5A$				
Forward Transconductance	$g_{FS}$	$V_{DS} = 25V, I_D = 10A$				
Source-drain voltage	$V_{SD}$	$I_S = 10A$				

**Electrical Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$f = 1MHz$	-	890	-	$\mu F$
Output capacitance	$C_{oss}$		-	423	-	
Reverse transfer capacitance	$C_{rss}$		-	8.1	-	

**Gate Charge characteristics ( $T_a = 25^\circ C$ )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = 25V$	-	11	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = 8A$	-	2.0	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS} = 10V$	-	1.2	-	

Note: ;



Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation

Fig.4 Typical output Characteristics

Fig.5 Threshold Voltage V.S Junction Temperature    Fig.6 Resistance V.S Drain Current

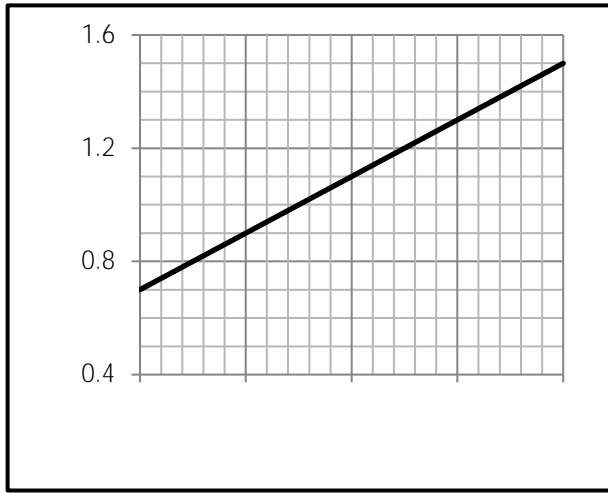


Fig.9 Switching Time Measurement Circuit

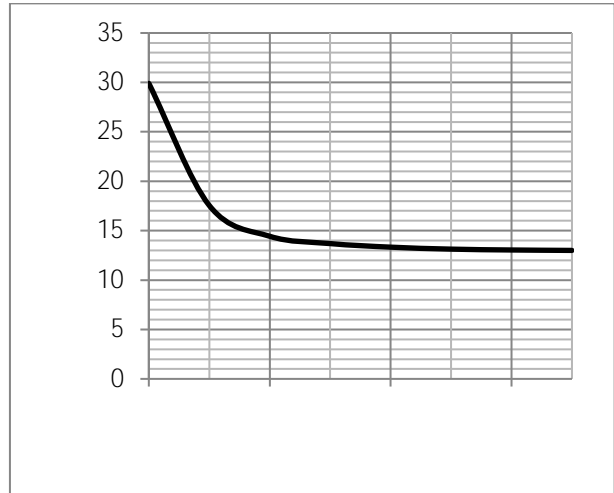


Fig.10 Gate Charge Waveform

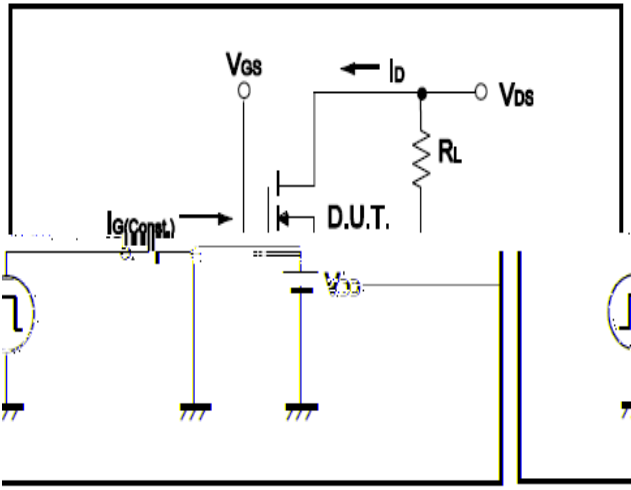


Fig.11 Switching Time Measurement Circuit

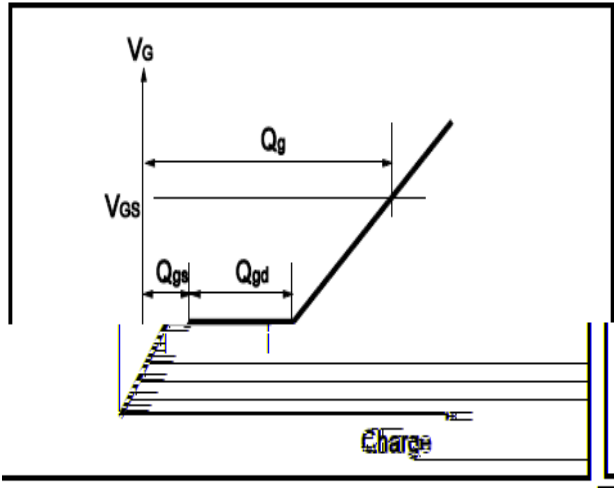


Fig.12 Gate Charge Waveform

